

ABSTRACT OF THE DISCLOSURE

Method for detecting whether the alignment of bit
line contacts and active areas in DRAM devices is normal,
and a test device thereof. In the present invention a
5 plurality of memory cells are formed in the memory area
and at least one test device is formed in the scribe line
region simultaneously. A first resistance and a second
resistance are detected by the test device. Normal
alignment of the bit line and the bar-type active area of
10 the test device is determined according to the first
resistance and the second resistance. Finally, whether
the alignment of the bit line contacts and the active
areas in memory areas is normal is determined according
to whether the alignment of the bit line contact and bar-
15 type active area of the test device is normal.